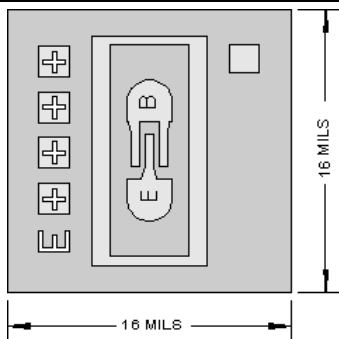


**Chip Type 2C918**  
**Geometry 0013**  
**Polarity NPN**

**Generic Packaged Parts:**  
**2N918**


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Chip type **2C918** by Semicoa Semiconductors provides performance similar to these devices.

#### Part Numbers:

2N918, 2N918UB, SD918, SD918F, SQ918, SQ918F

#### Product Summary:

**APPLICATIONS:** Designed for high frequency oscillator, multiplier and driver applications.

#### Features:

- High frequency rating

### Mechanical Specifications

|                  |                   |                     |
|------------------|-------------------|---------------------|
| Metallization    | Top               | Al - 15 kÅ min.     |
|                  | Backside          | Au - 6.5 kÅ nom.    |
| Bonding Pad Size | Emitter           | 2.7 mils x 2.7 mils |
|                  | Base              | 2.7 mils x 2.7 mils |
| Die Thickness    | 8 mils nominal    |                     |
| Chip Area        | 16 mils x 16 mils |                     |
| Top Surface      | Silox Passivated  |                     |

### Electrical Characteristics

 $T_A = 25^{\circ}\text{C}$ 

| Parameter     | Test conditions                                   | Min | Max | Unit |
|---------------|---------------------------------------------------|-----|-----|------|
| $BV_{CEO}$    | $I_C = 3.0 \text{ mA}, I_B = 0$                   | 15  | --- | V dc |
| $BV_{CBO}$    | $I_C = 10 \text{ } \mu\text{A}, I_E = 0$          | 30  | --- | V dc |
| $BV_{EBO}$    | $I_E = 10 \text{ } \mu\text{A}, I_C = 0$          | 3.0 | --- | V dc |
| $I_{CBO}$     | $V_{CB} = 15 \text{ V}, I_E = 0$                  | --- | 10  | nA   |
| $h_{FE}$      | $I_C = 3.0 \text{ mA dc}, V_{CE} = 1.0 \text{ V}$ | 20  | --- | ---  |
| $V_{CE(sat)}$ | $I_C = 30 \text{ mA dc}, I_B = 3.0 \text{ mA}$    | --- | 0.3 | V dc |

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu\text{s}$ , duty cycle less than 2%.